

## EF Series Power MOSFET with Fast Body Diode

### DESCRIPTION

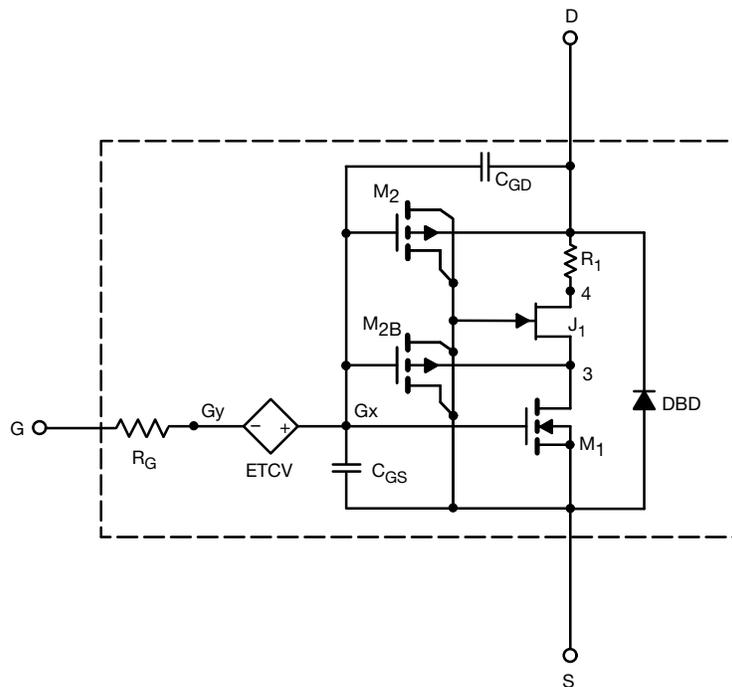
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the  $-55\text{ }^{\circ}\text{C}$  to  $150\text{ }^{\circ}\text{C}$  temperature ranges under the pulsed 0 V to 15 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### CHARACTERISTICS

- N-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- Apply for both linear and switching application
- Accurate over the  $-55\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$  temperature range
- Model the gate charge

### SUBCIRCUIT MODEL SCHEMATIC



### Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



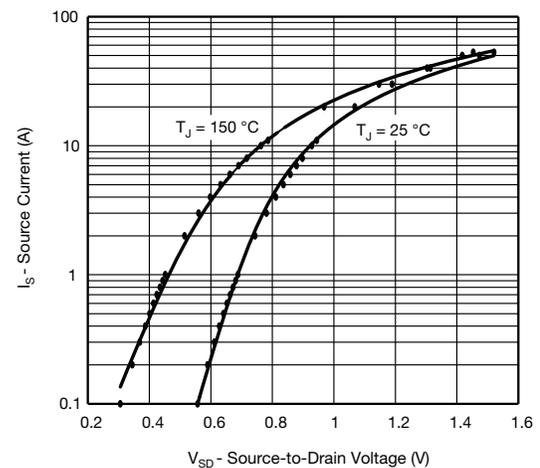
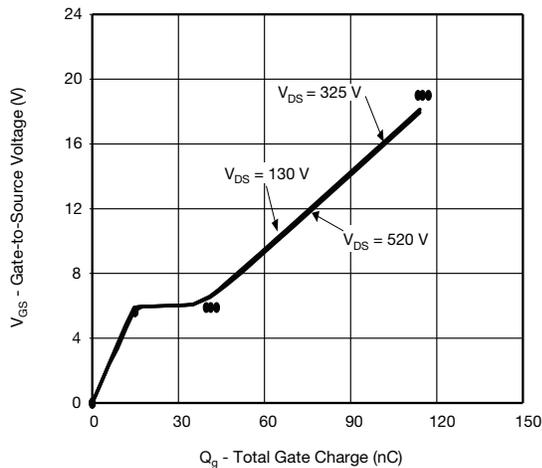
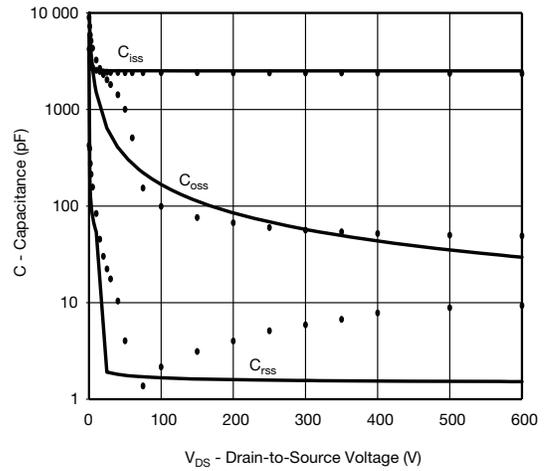
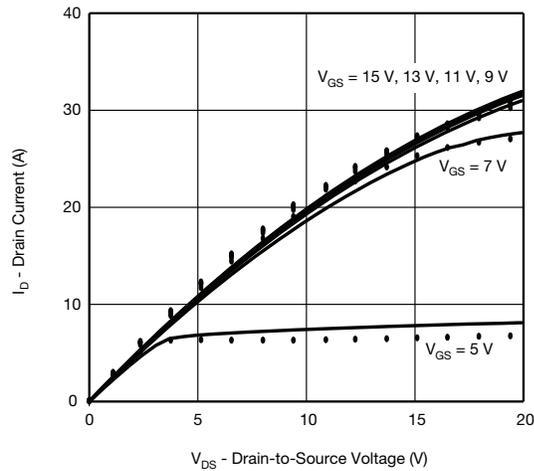
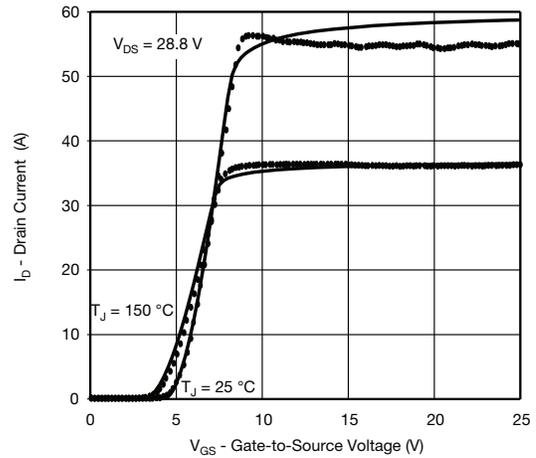
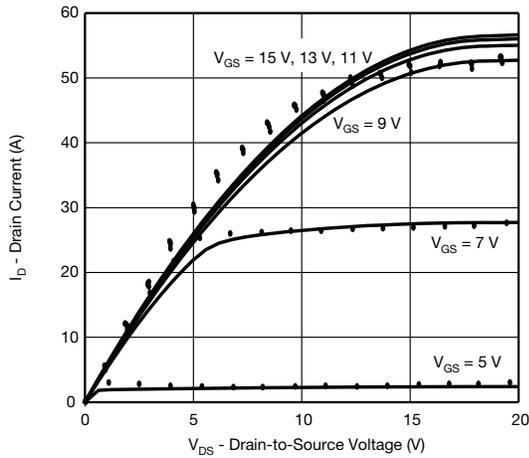
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
<b>Static</b>					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3	-	V
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 11\text{ A}$	0.182	0.157	$\Omega$
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 30\text{ V}, I_D = 11\text{ A}$	12	7.8	S
Diode Forward Voltage	$V_{SD}$	$I_S = 11\text{ A}, V_{GS} = 0\text{ V}$	0.94	0.95	V
<b>Dynamic <sup>b</sup></b>					
Input Capacitance	$C_{iss}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	2510	2396	pF
Output Capacitance	$C_{oss}$		170	99	
Reverse Transfer Capacitance	$C_{rss}$		2	2	
Total Gate Charge	$Q_g$	$V_{DS} = 520\text{ V}, V_{GS} = 10\text{ V}, I_D = 11\text{ A}$	65	68	nC
Gate-Source Charge	$Q_{gs}$		15	15	
Gate-Drain Charge	$Q_{gd}$		28	28	

**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.



## COMPARISON OF MODEL WITH MEASURED DATA ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



### Note

- Dots and squares represent measured data.

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